



UNITED STATES DEPARTMENT OF COMMERCE
Patent and Trademark Office
Address: COMMISSIONER OF PATENTS AND TRADEMARKS
Washington, D.C. 20231

APPLICATION NO.	FILING DATE	FIRST NAMED INVENTOR	ATTORNEY DOCKET NO.
08/903,453	07/29/97	FORBES	L 303.378US1

SCHWEGMAN LUNDBERG WOESSNER & KLUTH
PO BOX 2938
MINNEAPOLIS MN 55402
MMC2/1024

EXAMINER	
ECKERT II, G	
ART UNIT	PAPER NUMBER

2816

DATE MAILED:

10/24/00

Please find below and/or attached an Office communication concerning this application or proceeding.

Commissioner of Patents and Trademarks

BEST AVAILABLE COPY

Office Action Summary

Application No. 08/903,453	Applicant(s) Forbes et al.
Examiner George C. Eckert II	Group Art Unit 2815

Responsive to communication(s) filed on Aug 8, 2000

This action is FINAL.

Since this application is in condition for allowance except for formal matters, prosecution as to the merits is closed in accordance with the practice under *Ex parte Quayle*, 1935 C.D. 11; 453 O.G. 213.

A shortened statutory period for response to this action is set to expire 3 month(s), or thirty days, whichever is longer, from the mailing date of this communication. Failure to respond within the period for response will cause the application to become abandoned. (35 U.S.C. § 133). Extensions of time may be obtained under the provisions of 37 CFR 1.136(a).

Disposition of Claims

Claim(s) 1-6 and 20-64 is/are pending in the application.

Of the above, claim(s) _____ is/are withdrawn from consideration.

Claim(s) _____ is/are allowed.

Claim(s) 1-6 and 20-64 is/are rejected.

Claim(s) _____ is/are objected to.

Claims _____ are subject to restriction or election requirement.

Application Papers

See the attached Notice of Draftsperson's Patent Drawing Review, PTO-948.

The drawing(s) filed on _____ is/are objected to by the Examiner.

The proposed drawing correction, filed on _____ is approved disapproved.

The specification is objected to by the Examiner.

The oath or declaration is objected to by the Examiner.

Priority under 35 U.S.C. § 119

Acknowledgement is made of a claim for foreign priority under 35 U.S.C. § 119(a)-(d).

All Some* None of the CERTIFIED copies of the priority documents have been received.

received in Application No. (Series Code/Serial Number) _____.

received in this national stage application from the International Bureau (PCT Rule 17.2(a)).

*Certified copies not received: _____

Acknowledgement is made of a claim for domestic priority under 35 U.S.C. § 119(e).

Attachment(s)

Notice of References Cited, PTO-892

Information Disclosure Statement(s), PTO-1449, Paper No(s). 20

Interview Summary, PTO-413

Notice of Draftsperson's Patent Drawing Review, PTO-948

Notice of Informal Patent Application, PTO-152

-- SEE OFFICE ACTION ON THE FOLLOWING PAGES --

DETAILED ACTION

Continued Prosecution Application

The request filed on August 8, 2000 for a Continued Prosecution Application (CPA) under 37 CFR 1.53(d) based on parent Application No. 08/903,453 is acceptable and a CPA has been established. An action on the CPA follows.

Double Patenting

The nonstatutory double patenting rejection is based on a judicially created doctrine grounded in public policy (a policy reflected in the statute) so as to prevent the unjustified or improper timewise extension of the "right to exclude" granted by a patent and to prevent possible harassment by multiple assignees. See *In re Goodman*, 11 F.3d 1046, 29 USPQ2d 2010 (Fed. Cir. 1993); *In re Longi*, 759 F.2d 887, 225 USPQ 645 (Fed. Cir. 1985); *In re Van Ornum*, 686 F.2d 937, 214 USPQ 761 (CCPA 1982); *In re Vogel*, 422 F.2d 438, 164 USPQ 619 (CCPA 1970); and, *In re Thorington*, 418 F.2d 528, 163 USPQ 644 (CCPA 1969).

A timely filed terminal disclaimer in compliance with 37 CFR 1.321© may be used to overcome an actual or provisional rejection based on a nonstatutory double patenting ground provided the conflicting application or patent is shown to be commonly owned with this application. See 37 CFR 1.130(b).

Effective January 1, 1994, a registered attorney or agent of record may sign a terminal disclaimer. A terminal disclaimer signed by the assignee must fully comply with 37 CFR 3.73(b).

Claims 1-6 are provisionally rejected under the judicially created doctrine of obviousness-type double patenting as being unpatentable over claims 11-18 of co-pending Application No. 08/902,843. Although the conflicting claims are not identical, they are not patentably distinct from each other because the present invention and co-pending Application no. 08/902,843 disclose a transistor having:

a source and a drain separated by a channel supported by a semiconductor substrate;

a floating gate formed between the source and the drain above the channel and separated by an insulative amorphous carburized silicon layer;

a control gate formed adjacent to and insulated from the floating gate;

wherein the transistor is part of a memory cell comprising a capacitor.

Further, stacked capacitors are well known and widely used in memory devices.

This is a provisional obviousness-type double patenting rejection because the conflicting claims have not in fact been patented.

Claim Rejections - 35 USC § 102

The following is a quotation of the appropriate paragraphs of 35 U.S.C. 102 that form the basis for the rejections under this section made in this Office action:

A person shall be entitled to a patent unless --

(b) the invention was patented or described in a printed publication in this or a foreign country or in public use or on sale in this country, more than one year prior to the date of application for patent in the United States.

Claims 4, 5, 20, 23, 29, 32 and 36 are rejected under 35 U.S.C. 102(b) as being anticipated by Sakata et al., *Amorphous silicon/amorphous silicon carbide heterojunctions applied to memory device structures*, Electronics Letters, April 28, 1994, Vol. 30, No. 9.

With regard to claim 4, Sakata et al. teach in figure 1, a capacitive device comprising:

a first conductor layer shown as the a-Si:H layer which is supported by the substrate;

a dielectric layer of amorphous silicon carbide, shown as the a-SiC:H layer, formed on top of the first conductor layer; and

a second conductor layer shown as metal and formed on top of the dielectric layer.

With regard to claim 5, Sakata et al. teach that the layers extend substantially vertically from a general surface of the substrate. With regard to claim 20, Sakata et al. teach that the device may be used in a floating gate memory device (last paragraph in first column on page 688) wherein the a-Si:H layer is a floating gate and a layer of amorphous silicon carbide is between the floating gate and the substrate. With regard to claim 23, Sakata et al. teach under *Sample preparation* that the substrate is crystalline silicon doped n- or p-type. With regard to claims 29, 32 and 36, Sakata et al. teach the first conductive layer of a-Si:H supported by the substrate, the layer of amorphous SiC:H there over, and a second conductive layer of metal over the layer of a-SiC:H. The different intended uses cited in the preambles of these claims are not sufficient to establish patentability over that taught by Sakata et al., since the device of Sakata et al. is a semiconductor device which may be used as a memory cell and is inherently capacitive.

Claim Rejections - 35 USC § 103

The following is a quotation of 35 U.S.C. 103(a) which forms the basis for all obviousness rejections set forth in this Office action:

(a) A patent may not be obtained though the invention is not identically disclosed or described as set forth in section 102 of this title, if the differences between the subject matter sought to be patented and the prior art are such that the subject matter as a whole would have been obvious at the time the invention was made to a person having ordinary skill in the art to which said subject matter pertains. Patentability shall not be negated by the manner in which the invention was made.

Claims 1-3, 6, 21, 22, 24-30, 33-34, 37, 39, 41, 44-46 and 50 are rejected under 35 U.S.C. 103(a) as being unpatentable over Sakata et al. With regard to these claims and as

discussed above, Sakata et al. have taught the structure of a floating gate device having a doped monocrystalline silicon substrate, a graded amorphous silicon carbide layer thereon, an amorphous silicon layer to serve as a floating gate, a second amorphous silicon carbide layer thereon, and a metal layer to serve as a control gate. Sakata et al. do not expressly disclose the device comprising source, drain or channel regions. However, because Sakata et al. do teach that the device can be applied as a memory device, specifically a floating gate device, these features are considered obvious. Sakata et al. further state on page 689 that the device can be used as a dynamic random access memory (DRAM). Both a floating gate device (typically used as an erasable programmable read only memory device or EPROM) and a DRAM device comprise source/drain and channel regions to effect a transistor capable of memory functions. Also, it is well known in the art that appropriate circuitry such as word lines and bit lines are required to effect a memory array.

Regarding the limitations that the substrate comprises a semiconductor surface layer on an underlying insulating portion, such limitation is also considered obvious. Placing a semiconducting layer on an underlying insulating layer results in a device commonly referred to as silicon-on-insulator (SOI). By placing the semiconducting layer above an insulator, several advantages are realized. SOI reduces capacitive coupling between various circuit elements over the entire IC chip, reduces chip size and/or increases packing density, and minimum device separation is determined only by the limitations of lithography. Therefore the claimed limitations that the

device be formed over an underlying insulating portion are also considered obvious changes over that taught by Sakata et al.

Finally, the limitations that the substrate is p-type while the source and drain regions are n-type, are considered obvious over that taught by Sakata et al. First, Sakata et al. teach that the substrate may be formed having a p-type conductivity (see column 2, under *Sample preparation*). As such, because it is well known that a transistor formed in a p-type substrate will also be formed with n-type source/drain regions (to form an NMOS transistor), those limitations in the instant claims are considered obvious.

Claims 31, 35, 38, 40, 42, 43, 47-49 and 51-64 are rejected under 35 U.S.C. 103(a) as being unpatentable over Sakata et al. as applied above, and further in view of Sugita et al. (of record). Sakata et al. taught the device of claims 1, 2, 3, 21, 29, 32, 36, 46 and 50 as discussed above. However, the device was not taught wherein the conductive layers which constitute the floating and control gates comprise polysilicon. Sugita et al. teaches a device using a silicon carbide insulator wherein the floating gate 6 is polysilicon. Polysilicon is well known as a gate conductor in the art. Its use as the control gate electrode is considered an obvious change over that taught by Sakata et al., especially in light of the use of polysilicon as a floating gate as taught by Sugita et al.

Sakata et al. and Sugita et al. are combinable because they are from the same field of endeavor. At the time of the invention it would have been obvious to a person of ordinary skill in

the art to use the polysilicon as taught by Sugita et al. in the device of Sakata et al. The motivation for doing so is that polysilicon is a well known conductor in the art as established by Sugita et al. Therefore, it would have been obvious to combine Sakata et al. with Sugita et al. to obtain the invention of claims 31, 35, 38, 40, 42, 43, 47-49 and 51-64.

Conclusion

Any inquiry concerning this communication or earlier communications from the examiner should be directed to George C. Eckert II whose telephone number is (703) 305-2752.

Any inquiry of a general nature or relating to the status of this application or proceeding should be directed to the Group receptionist whose telephone number is (703) 308-0956.

GCE
October 20, 2000



EDDIE C. LEE
PRIMARY EXAMINER